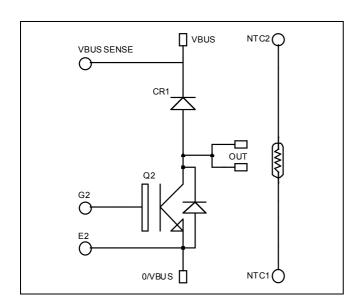


# Boost chopper NPT IGBT Power Module

$$V_{CES} = 600V$$
  
 $I_C = 180A$  @  $Tc = 80$ °C



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#### **Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

#### **Benefits**

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive T<sub>C</sub> of V<sub>CEsat</sub>
- Low profile
- RoHS compliant

### Absolute maximum ratings

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	Symbol	Parameter		Max ratings	Unit
ı	$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
ı	т	Continuous Collector Current	$T_c = 25^{\circ}C$	220	
	I <sub>C</sub> Continuous Collector Current	Continuous Conector Current	$T_c = 80$ °C	180	A
	$I_{CM}$	Pulsed Collector Current	$T_c = 25^{\circ}C$	630	
	$V_{GE}$	Gate – Emitter Voltage		±20	V
	$P_{D}$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	833	W
	RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	400A @ 600V	

OUT

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NTC2 #

NTC1 B

TAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$			300	μA	
1CES	Zero Gate Voltage Concetor Current	$V_{CE} = 600V$	$T_{i} = 125^{\circ}C$			1000	μΛ
17	Callantan Emittan actuaction Walters	$V_{GE} = 15V$		2.0	2.5	V	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$I_C = 180A$ $T_j = 125^{\circ}C$		2.2		v	
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$ $V_{GE} = 20 \text{ V}, V_{CE} = 0\text{ V}$		3		5	V
$I_{GES}$	Gate – Emitter Leakage Current					±200	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			8.6		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			0.94		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			0.8		
$Q_g$	Total gate Charge	$V_{GS} = 15V$			660		nC
$Q_{ge}$	Gate – Emitter Charge	$V_{Bus} = 300V$			580		
$Q_{gc}$	Gate – Collector Charge	$I_{\rm C} = 180 {\rm A}$			400		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 180A$ $R_{G} = 2.5 \Omega$			26		ns
$T_{\rm r}$	Rise Time				25		
$T_{d(off)}$	Turn-off Delay Time				150		
$T_{\mathrm{f}}$	Fall Time				30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 180A$ $R_{G} = 2.5 \Omega$			26		ns
$T_{\rm r}$	Rise Time				25		
$T_{d(off)}$	Turn-off Delay Time				170		
$T_{\rm f}$	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$	$T_j = 125$ °C		8.6		I
$E_{\text{off}}$	Turn-off Switching Energy	$I_C = 180A$ $R_G = 2.5 \Omega$	$T_j = 125$ °C		7		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600V$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$			350	μΑ	
1KM	Waximum Reverse Bearage Current		VR OOOV	$T_j = 125$ °C			750
$I_F$	DC Forward Current		$T_c = 80$ °C		200		A
		$I_F = 200A$			1.6	1.8	
$V_{\rm F}$	Diode Forward Voltage	$I_F = 400A$			1.9		V
		$I_F = 200A$	$T_j = 125$ °C		1.4		
$t_{rr}$	Reverse Recovery Time $ I_F = 200A \\ V_R = 400V $ $ T_j = 25^{\circ}C $ $ T_j = 125^{\circ}C $		$T_j = 25$ °C		180		ns
ι <sub>rr</sub>		$I_F = 200A$ $V_P = 400V$		220		113	
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 400A/\mu s$	$T_j = 25^{\circ}C$		780		пC
₹rr	reverse receivery charge		$T_{j} = 125^{\circ}C$		2900		110



## Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.15	°C/W
1\(\text{thJC}\)			Diode			0.32	C/ VV
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
$T_{J}$	Operating junction temperature range		-40		150		
T <sub>STG</sub>	Storage Temperature Range Operating Case Temperature		-40		125	°C	
$T_{\rm C}$			-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

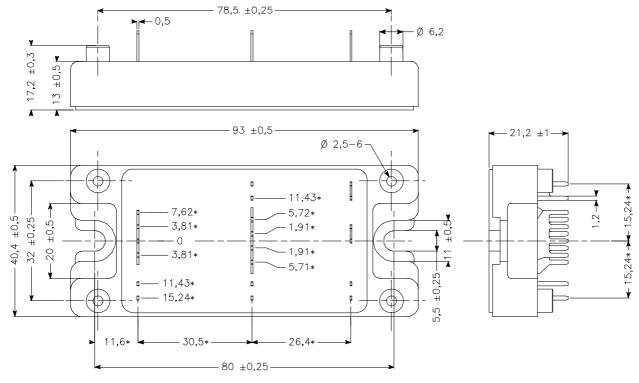
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

## SP4 Package outline (dimensions in mm)

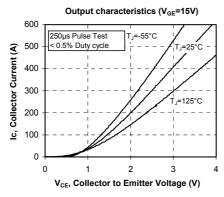


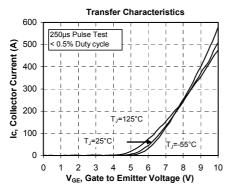
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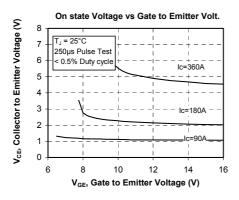
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

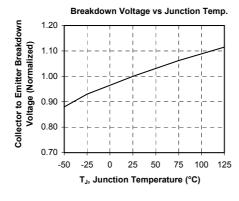


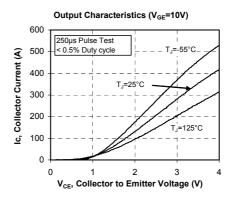
## **Typical Performance Curve**

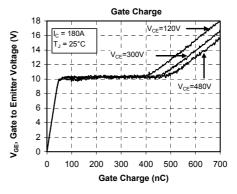


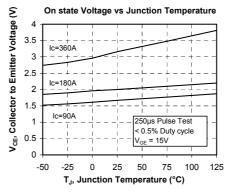


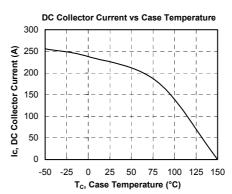




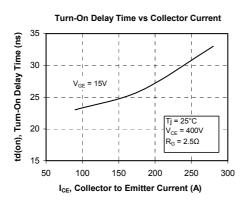


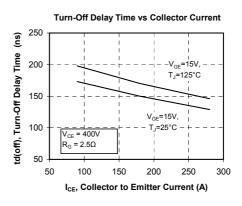


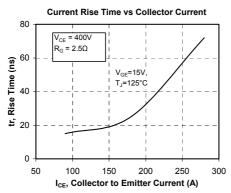


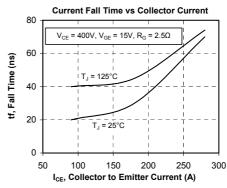


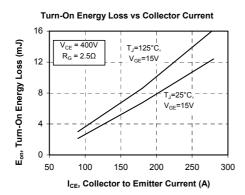


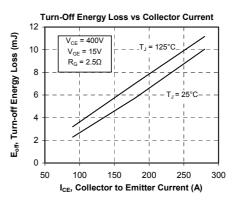


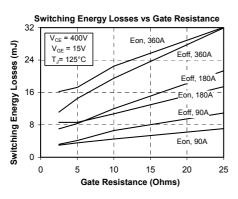


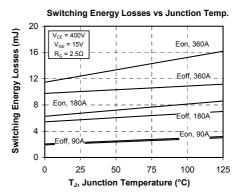




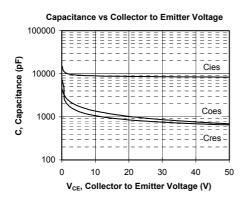


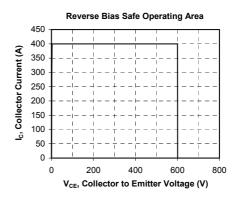


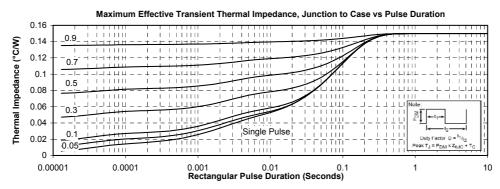


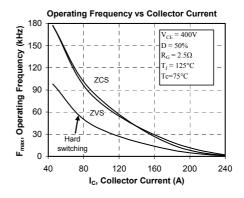














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